

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/630969	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:12
L3	11147	438/240,216,287,585-591,591, 770-778.CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:21
L4	3125	3 and chamber	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:22
L5	142	4 and first adj oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:22
L6	101	5 and second adj oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:23
L7	0	(semiconductor ADJ microstructure ADJ positioning AND initial ADJ dielectric ADJ layer AND process ADJ chamber AND flowing WITH gas WITH oxygen ADJ gas AND chambe AND oxide ADJ layer WITH high ADJ thickness ADJ uniformity WITH oxide AND self ADJ limiting WITH oxidation ADJ process AND partial ADJ pressure oxygen ADJ containing WITH chamber WITH less ADJ than AND "50" ADJ Torr AND first AND second AND oxide).CLM.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 13:01

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	50	self near3 limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L3	61	self near3 limiting near5 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L4	66	self near3 limiting near6 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L5	95	self near3 limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
L6	95	self with limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
S58	1	10/630969	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:16
S59	7144	oxide with low adj pressure	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S60	476	S59 and (oxide low adj pressure) with torr	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S61	478	S59 and (oxide low adj pressure) with (torr pascal)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18
S62	479	S59 and (oxide low adj pressure) with (torr pascal atmospheric)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18

S63	370	S62 and (oxide with (thick thickness thicker))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:19
S64	146	S63 and ((oxide thick thickness thicker) with angstrom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:20
S65	74	S64 and (oxide with (oxygen 'o2' oxygen adj containing))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:24
S66	206	oxide with self adj limiting near3 oxid\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:55
S67	50	oxide with self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:56
S68	163	self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:57
S69	50	self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35



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558: (1) 10/630969

--S59: (71 44) oxide with low adj pres:

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Q8a US-PGPUB:USPAT:EPO:JPO

Default operator: **OR**

self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide

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[ISLA form](#)
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[Text](#)
[HTML](#)

	U	1	Document ID	Issue Dat	Page	Title	Current O	Current X	Retrieval
20	r	r	US 6559069 B2	2003050	13	Process for the electrochemical oxidation of a semiconductor	438/770	257/E21.2	
21	r	r	US 6492283 B2	2002121	11	Method of forming ultrathin oxide layer	438/770	257/E21.1	
22	r	r	US 6444592 B1	2002090	6	Interfacial oxidation process for high-k gate dielectric process	438/770	257/E21.2	
23	r	r	US 6417564 B2	2002070	3	Semiconductor element with metal layer	257/740	257/763;	
24	r	r	US 6329722 B1	2001121	7	Bonding pads for integrated circuits having copper interconnect	257/786	257/690;	
25	r	r	US 6197641 B1	2001030	17	Process for fabricating vertical transistors	438/268	257/E21.4	
26	r	r	US 6165914 A	2000122	5	Method for fabricating semiconductor devices with thick high-k	438/787	257/E21.2	
27	r	r	US 6144071 A	2000110	18	Ultrathin silicon nitride containing sidewall spacers for improved	257/344	257/384;	
28	r	r	US 6103595 A	2000081	6	Assisted local oxidation of silicon	438/431	257/E21.5	
29	r	r	US 6063665 A	2000051	6	Method for silicon surface control for shallow junction formation	438/260	257/E21.3	
30	r	r	US 5961791 A	1999100	11	Process for fabricating a semiconductor device	204/192.1	204/192.15	
31	r	r	US 5916378 A	1999062	10	Method of reducing metal contamination during semiconductor	148/243	148/275;	
32	r	r	US 5804910 A	1998090	7	Field emission displays with low function emitters and metal	313/310		
33	r	r	US 5661073 A	1997082	6	Method for forming field oxide having uniform thickness	438/431	257/E21.5	
34	r	r	US 5589422 A	1996123	16	Controlled, gas phase process for removal of trace metal contamination	438/476	134/1.3;	
35	r	r	US 5359216 A	1994102	9	DRAM process with improved polysilicon-to-polysilicon conversion	257/306	257/297;	
36	r	r	US 5334281 A	1994080	7	Method of forming thin silicon mesas having uniform thickness	438/404	148/DIG.5	
37	r	r	US RE34535 E	1994020	9	Floating gate memory with improved dielectric	365/185.0	257/319;	
38	r	r	US 5244825 A	1993091	8	DRAM process with improved poly-to-poly capacitor	438/241	257/E27.0	
39	r	r	US 5104910 A	1992041	12	Fabrication of interpoly dielectric for EPROM-related technology	438/502	257/E21.2	

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File View Edit Tools Window Help								
<div> <div> Failed Saved SS8: (1) 10/630969 SS9: (7144) oxide with low adj pres </div> <div> US-PG-PUB:USPAT:EPG:JPO Default period: 0A self adj limiting near3 (oxidizing oxidation oxidized oxidation) with oxide BRS form 151A form 22 Image 1 Test HTML </div> </div>								
	U	Document ID	Issue Dat	Page	Title	Current O	Current X	Retrieval
32	r	US 5804910 A	1998090	7	Field emission displays with low function emitters and met	313/310		
33	r	US 5661073 A	1997082	6	Method for forming field oxide having uniform thickness	438/431	257/E21.5	
34	r	US 5589422 A	1996123	16	Controlled, gas phase process for removal of trace metal co	438/476	134/1.3;	
35	r	US 5359216 A	1994102	9	DRAM process with improved polysilicon-to-polysilicon c	257/306	257/297;	
36	r	US 5334281 A	1994080	7	Method of forming thin silicon mesas having uniform thick	438/404	148/DIG.5	
37	r	US RE34535 E	1994020	9	Floating gate memory with improved dielectric	365/185.0	257/319;	
38	r	US 5244825 A	1993091	8	DRAM process with improved poly-to-poly capacitor	438/241	257/E27.0	
39	r	US 5104819 A	1992041	13	Fabrication of interpoly dielectric for EPROM-related techn	438/593	257/E21.2	
40	r	US 5098192 A	1992032	10	DRAM with improved poly-to-poly capacitor	257/306	257/760;	
41	r	US 4949154 A	1990081	11	Thin dielectrics over polysilicon	257/311	257/371;	
42	r	US 4922312 A	1990050	8	DRAM process with improved polysilicon-to-polysilicon c	257/297	257/300;	
43	r	US 4697330 A	1987100	10	Floating gate memory process with improved dielectric	438/261	257/E21.6	
44	r	US 4656729 A	1987041	11	Dual electron injection structure and process with self-limit	438/261	257/316;	
45	r	US 4613956 A	1986092	8	Floating gate memory with improved dielectric	365/185.0	257/315;	
46	r	US 4577390 A	1986032	11	Fabrication of polysilicon to polysilicon capacitors with a c	438/396	257/371;	
47	r	US 4405659 A	1983092	9	Method for producing columnar grain ceramic thermal barr	427/248.1	427/250;	
48	r	US 4401697 A	1983083	10	Method for producing columnar grain ceramic thermal barr	427/250	204/192.15	
49	r	US 4321311 A	1982032	9	Columnar grain ceramic thermal barrier coatings	428/623	428/629;	
50	r	WO 2005013348 A	2005021		FORMATION OF ULTRA-THIN OXIDE AND OXYNITRI		257/E21.2	